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Kawase et al.

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(54) **SEMICONDUCTOR DEVICE**

(71) Applicant: **Mitsubishi Electric Corporation**, Chiyoda-ku, Tokyo (JP)

(72) Inventors: **Tatsuya Kawase**, Tokyo (JP); **Noboru Miyamoto**, Tokyo (JP); **Mikio Ishihara**, Tokyo (JP)

(73) Assignee: **Mitsubishi Electric Corporation**, Tokyo (JP)

(**) Term: **14 Years**

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(30) **Foreign Application Priority Data**

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May 8, 2013 (JP) 2013-010102
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(51) **LOC (10) Cl.** **13-03**

(52) **U.S. Cl.**
USPC **D13/182**

(58) **Field of Classification Search**
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CPC H01L 21/00; H01L 21/02433; H01L 2224/42; H01L 2224/43; H01L 2021/00; H01L 2021/02; H01L 2021/04; H01L 21/4214; H01L 21/4846; H01L 21/4871; H01L 21/67144; H01L 23/12; H01L 23/13; H01L 23/14; H01L 23/147; H01L 2924/171; H01L 2924/1711; H01L 2924/1715; H01L 2924/17151; H01L 2924/181; H01L 2924/1811; H01L 2924/1815; H01L 2924/19042; H01L 2924/1905; H01L 2224/08054; H01L 23/58; H05B 41/14; H02B 6/4201; G02B 6/4256; G02B 6/4257; G02B 6/4261; G02B 6/4262; G02B 6/42; G02B 6/4281; H05K 1/14; H05K 1/141; H05K 1/142; H05K 1/144; H05K 1/18; H05K 1/181; H05K 1/182; H05K 1/026; H05K 1/0228; H05K 1/0245; H05K 1/0236; H05K 1/0263
See application file for complete search history.

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Primary Examiner — Elizabeth J Oswecki
(74) *Attorney, Agent, or Firm* — Sughrue Mion, PLLC; Richard C. Turner

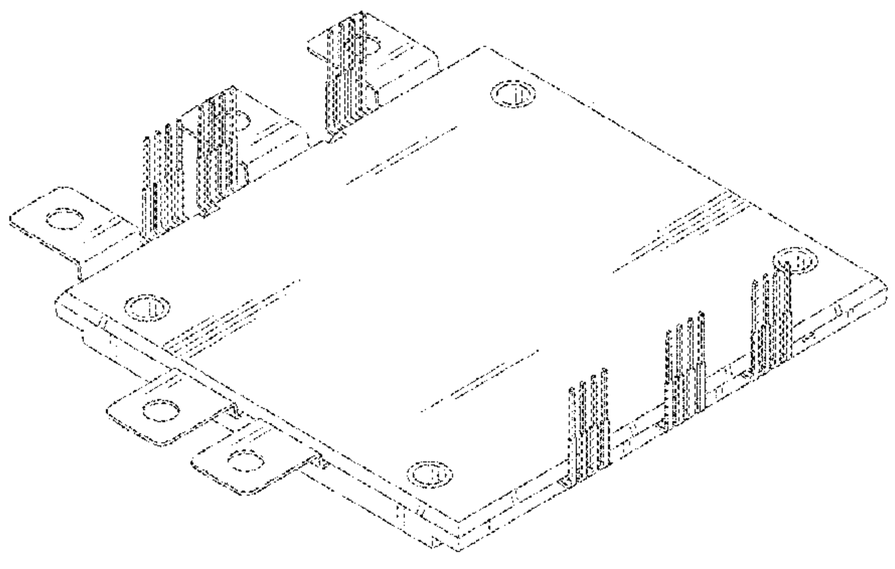
(57) **CLAIM**

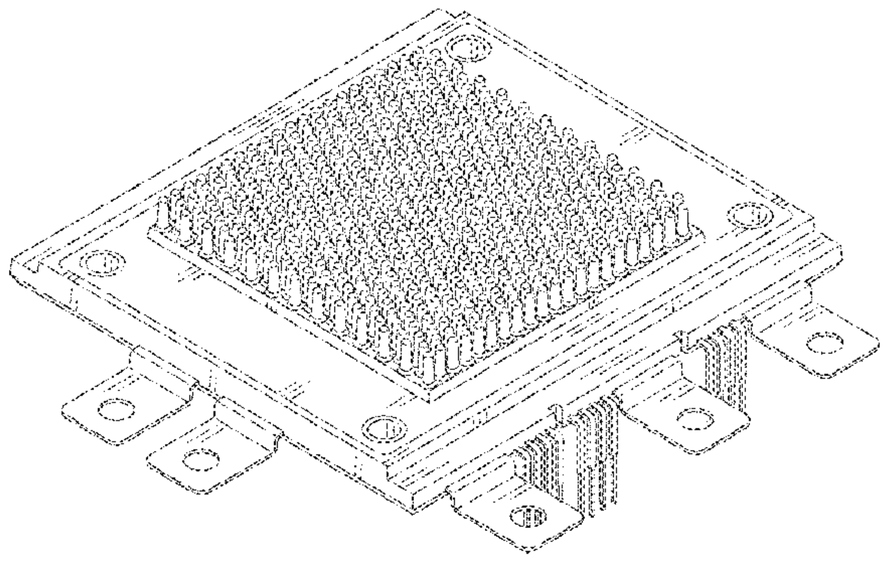
The ornamental design for a semiconductor device, as shown and described.

DESCRIPTION

FIG. **1** is a front, top and right side perspective view of a semiconductor device showing our new design;
FIG. **2** is a rear, top, and left side perspective view thereof;
FIG. **3** is a front elevational view thereof;
FIG. **4** is a rear elevational view thereof;
FIG. **5** is a left side elevational view thereof;
FIG. **6** is a right side elevational view thereof;
FIG. **7** is a top plan view thereof;
FIG. **8** is a bottom plan view thereof;
FIG. **9** is a front, top and right side perspective view thereof, shown in a used condition attached to a mount shown in broken lines; and,
FIG. **10** is another front elevational view thereof, attached to a mount shown in broken lines.
The broken lines shown in the drawings represent portions of the semiconductor device that form no part of the claimed design.

1 Claim, 8 Drawing Sheets





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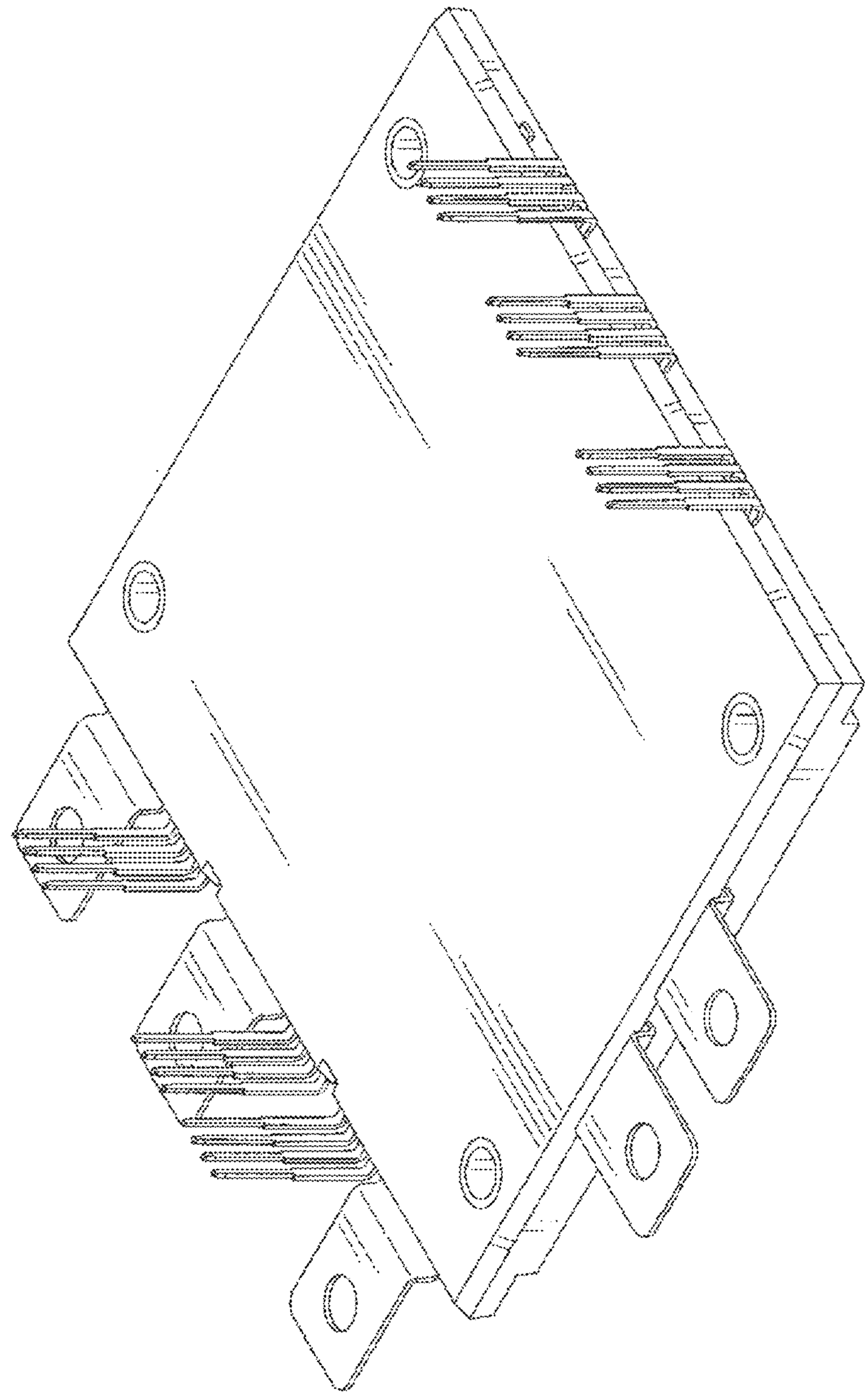


Fig. 1

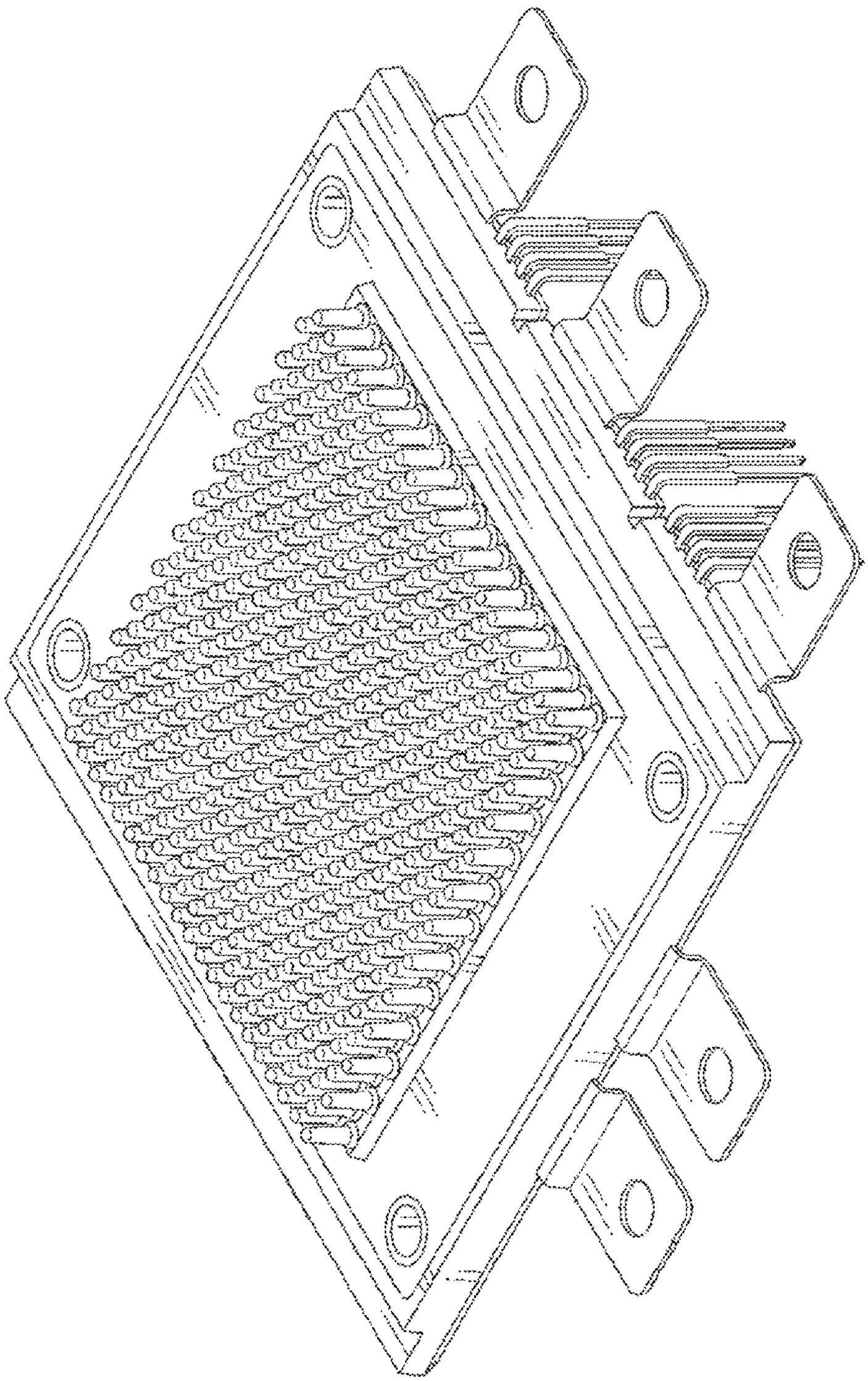
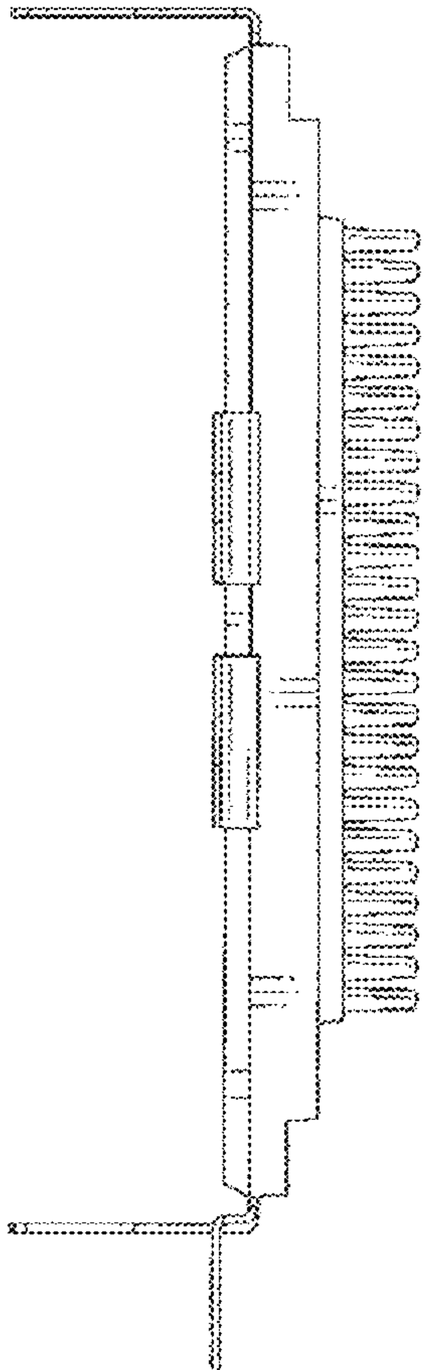


Fig. 2



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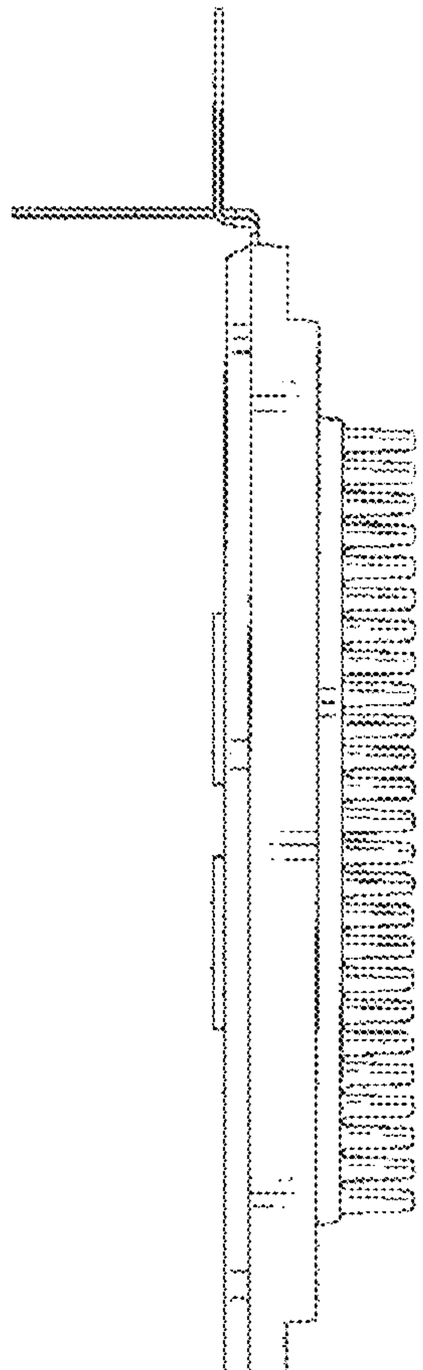


Fig. 4

Fig. 5

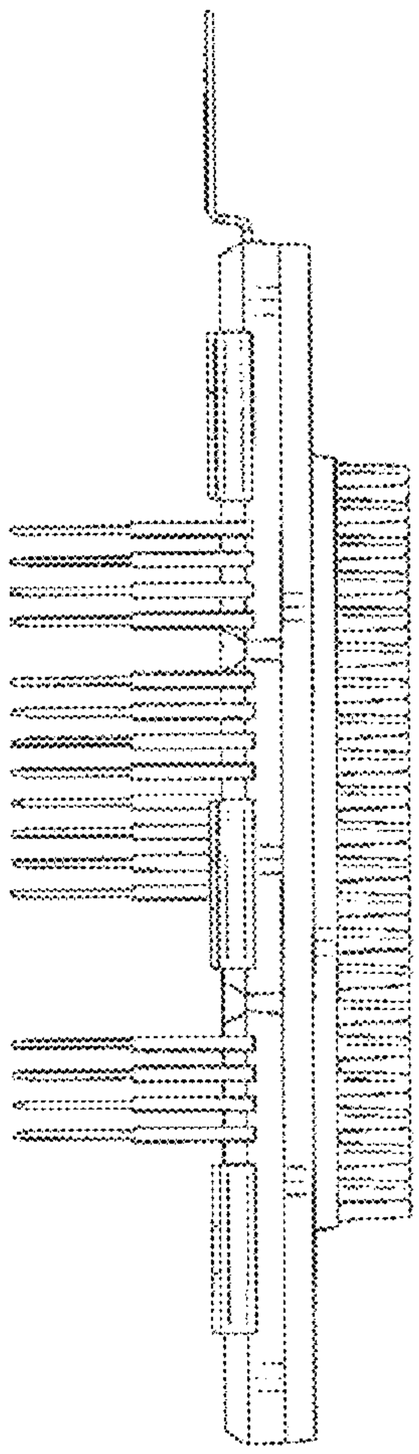
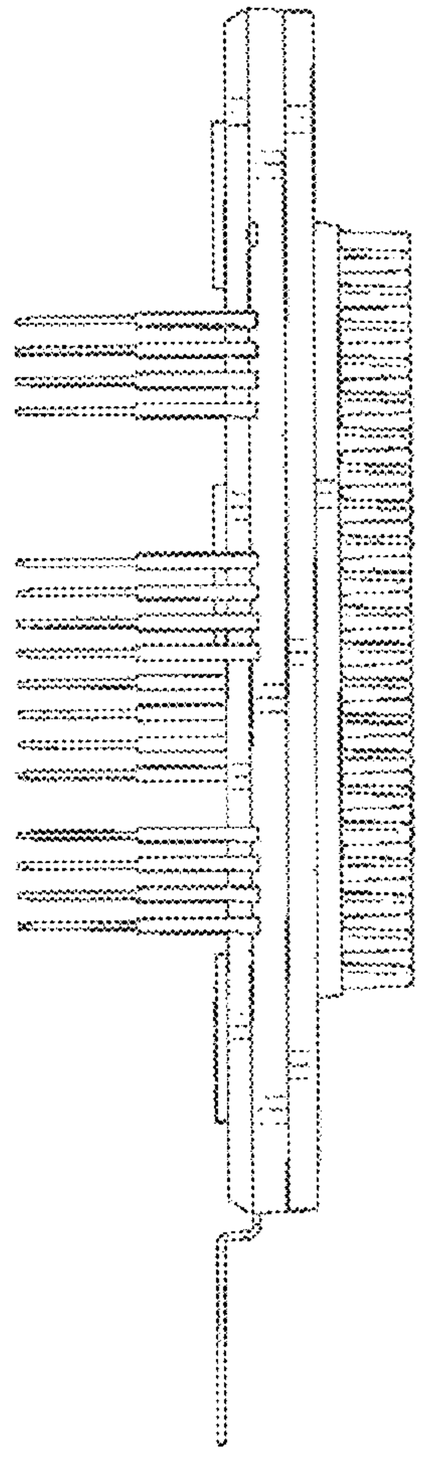


Fig. 6



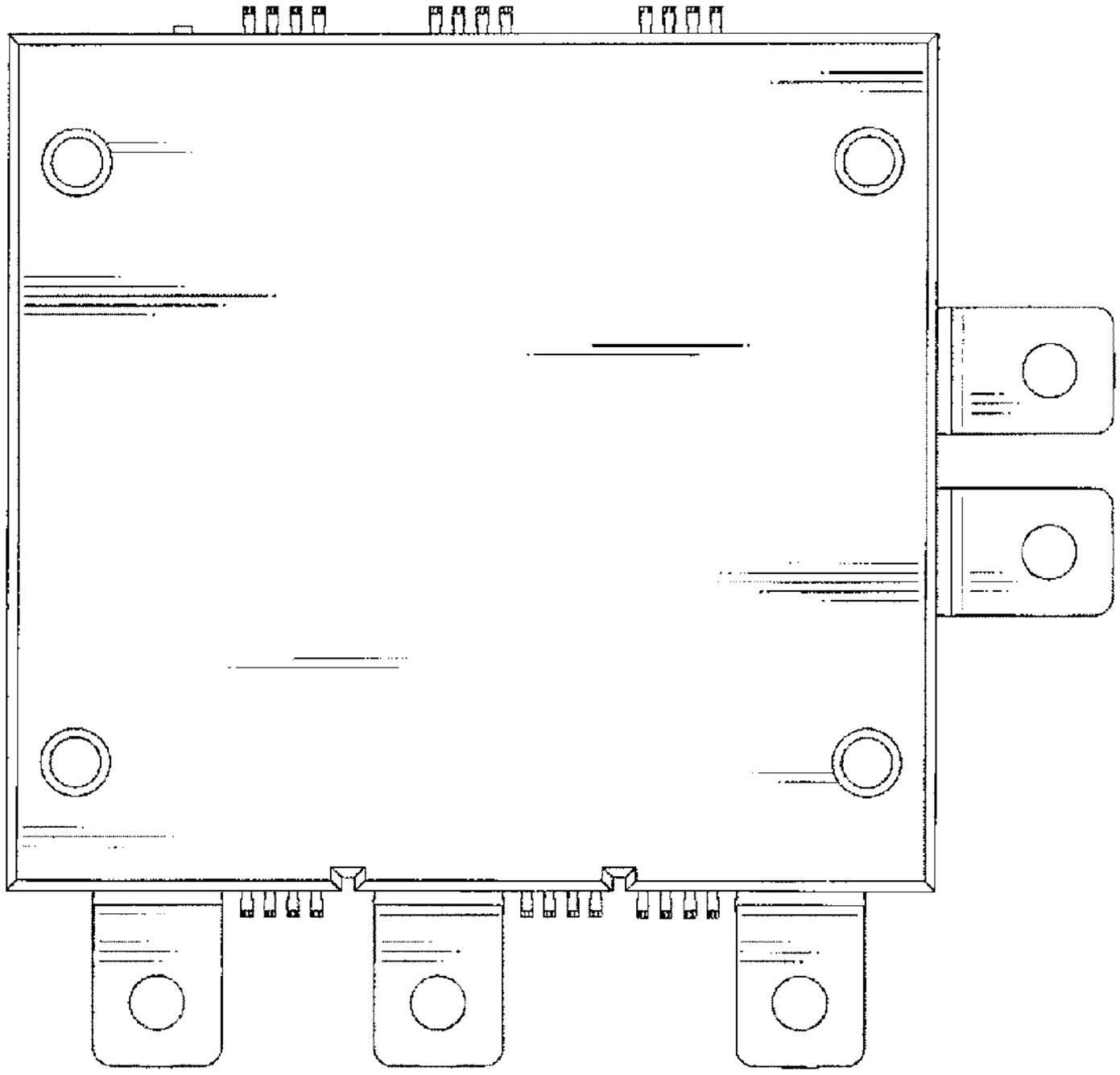
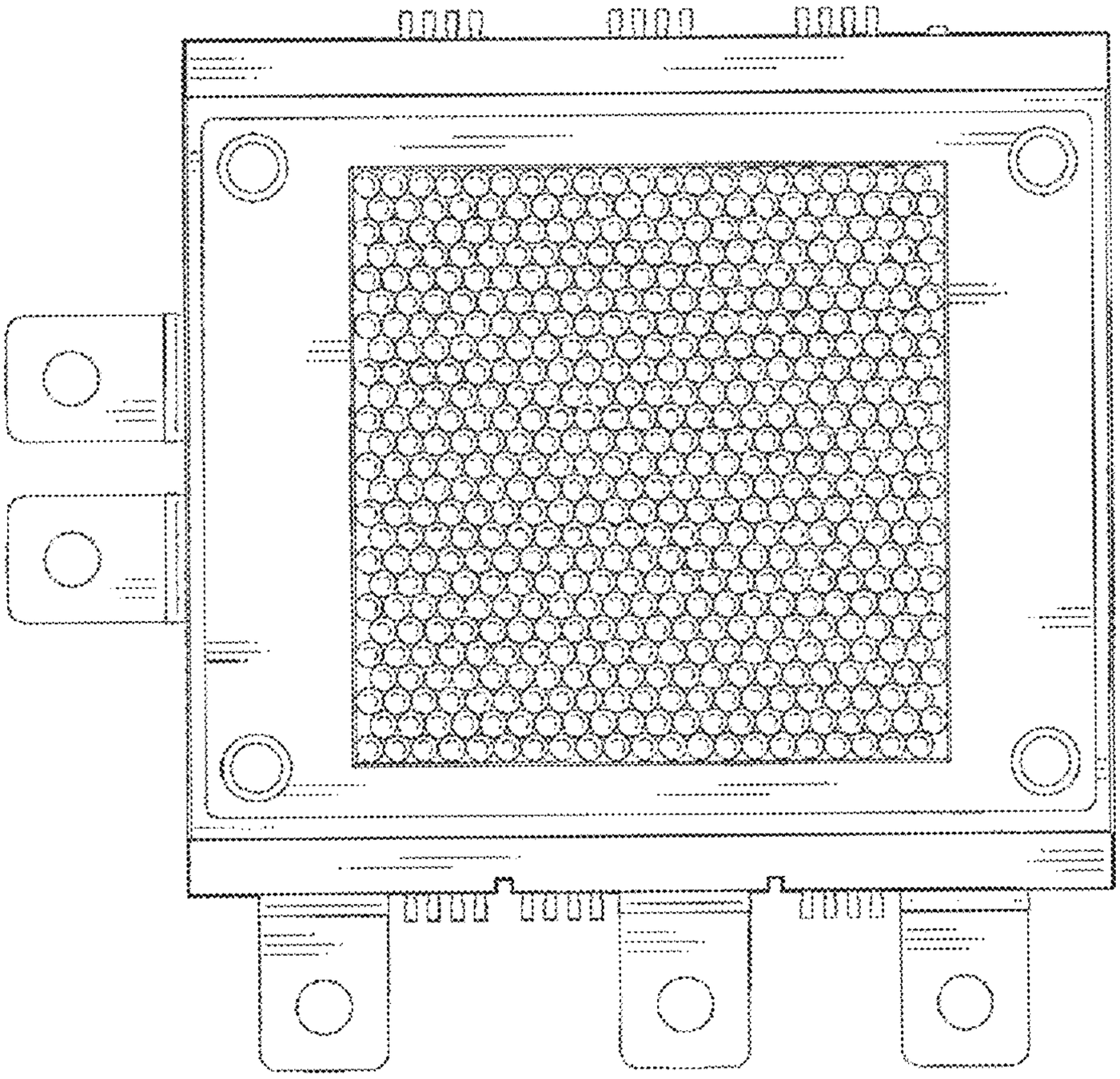


Fig. 7

Fig. 8



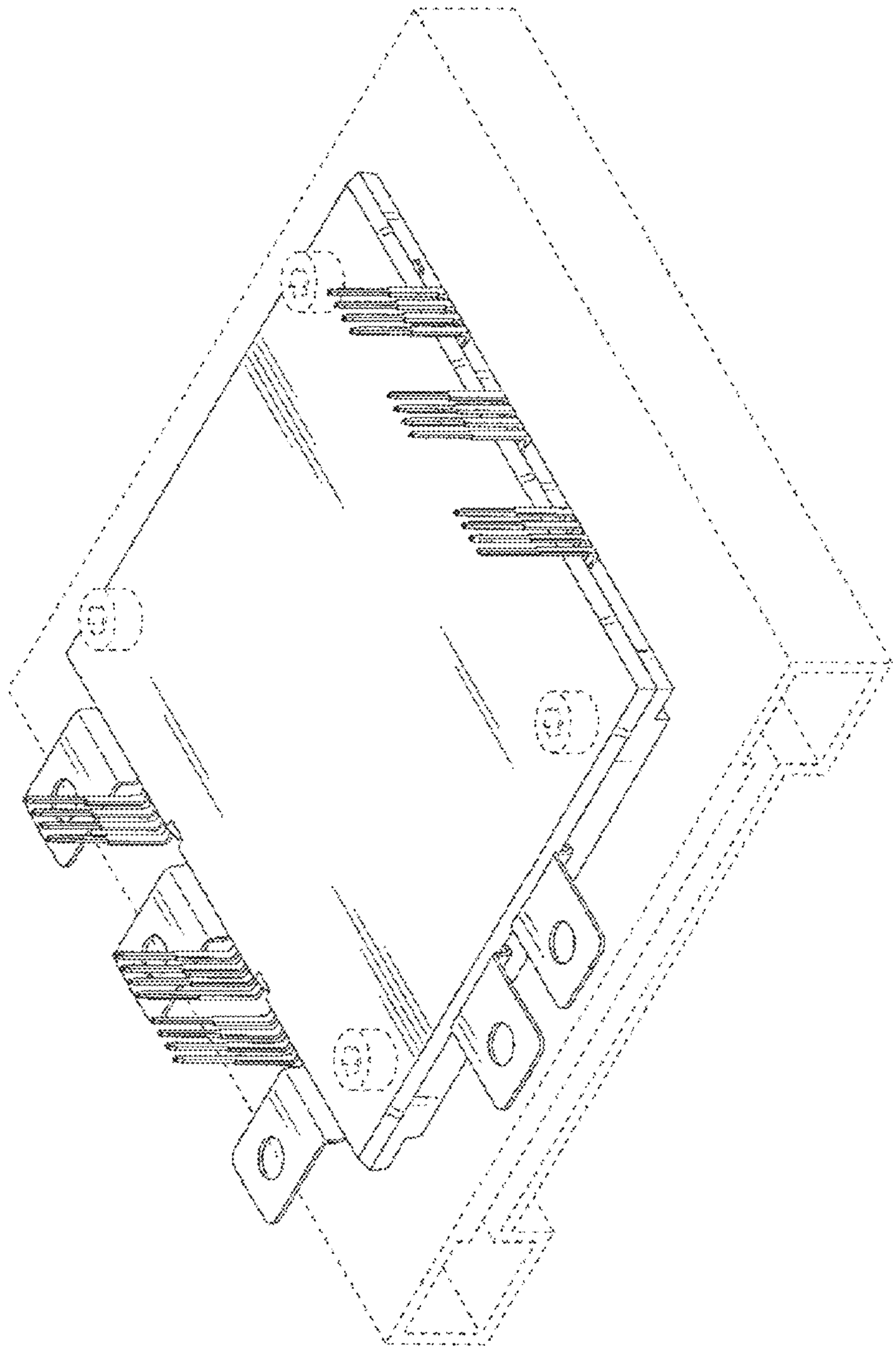


Fig. 9

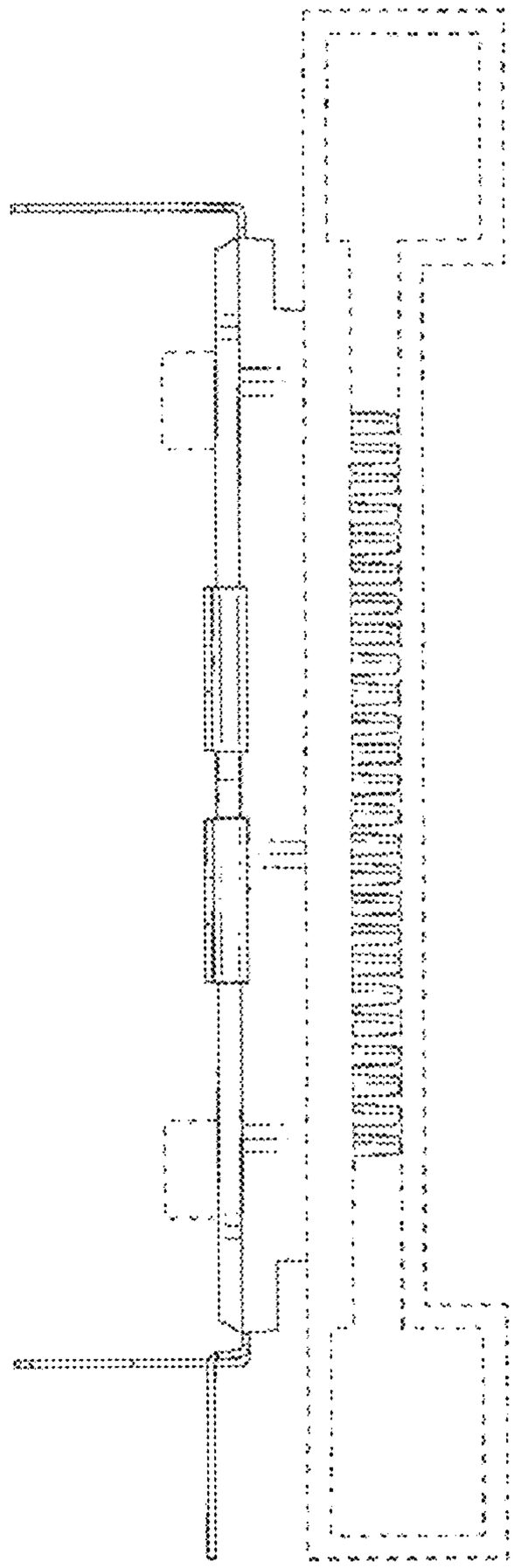


Fig. 10